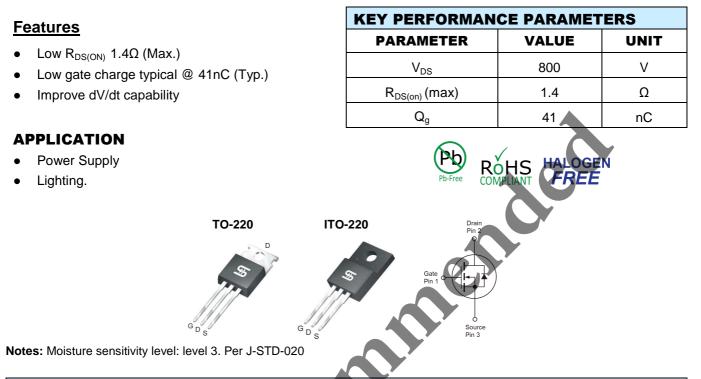


TSM8N80 Taiwan Semiconductor

N-Channel Power MOSFET

 $800V,\,8A,\,1.4\Omega$



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT	
Drain-Source Voltage	V _{DS}	800		V	
Gate-Source Voltage	V _{GS}	±30		V	
Continuous Drain Current (Note 4) $T_{C} = 25^{\circ}C$	- I _D	8		А	
$T_{\rm C} = 100^{\circ}{\rm C}$		4.9			
Pulsed Drain Current (Note 2)	I _{DM}	32		А	
Total Power Dissipation @ $T_c = 25^{\circ}C$	P _{DTOT}	250	40.3	W	
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	1	60	mJ	
Single Pulsed Avalanche Current (Note 3)	I _{AS}		8	А	
Repetitive Avalanche Energy	E _{AR}	2	25	mJ	
Peak Diode Recovery ^(Note 7)	dV/dt	4	.5	V	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	- 55 to	o +150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT	
Junction to Case Thermal Resistance	R _{ejc}	0.5	3.1	°C/W	
Junction to Ambient Thermal Resistance	R _{OJA}	62.5		°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)				•	•	•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	800			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2.0		4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	I _{DSS}			10	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 4.0A$	R _{DS(ON)}		1.1	1.4	Ω
Forward Transconductance	$V_{DS} = 30V, I_{D} = 4.0A$	g _{fs}		7		S
Diode Forward Voltage	$I_{\rm S} = 8$ A, $V_{\rm GS} = 0$ V	V _{SD}			1.5	V
Dynamic (Note 5)						
Total Gate Charge	$V_{DS} = 640V, I_D = 8.0A,$	Qg		41		
Gate-Source Charge		Q _{gs}		10		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}	-	11		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		1921		
Output Capacitance		C _{oss}		146		pF
Reverse Transfer Capacitance		C _{rss}		12		
Gate Resistance	F = 1MHz, open drain	R _g		2.9		Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 400V,$ $R_{GEN} = 25\Omega,$ $I_D = 8.0A, V_{GS} = 10V,$	t _{d(on)}		133		
Turn-On Rise Time		t _r		30		
Turn-Off Delay Time		t _{d(off)}		172		ns
Turn-Off Fall Time		t _f		37		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 8.0A, V _{GS} = 0V	V _{SD}			1.5	V
Reverse Recovery Time	V _{GS} =0V, I _S = 8A	t _{rr}		479		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		5.5		μC

Notes:

1. Current limited by package.

2. Pulse width limited by the maximum junction temperature.

3. L = 5mH, I_{AS} = 8A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25^oC.

4. Pulse test: PW \leq 300µs, duty cycle \leq 2%.

5. For DESIGN AID ONLY, not subject to production testing.

6. Switching time is essentially independent of operating temperature.

7. $I_{SD} \le 8A$, dl/dt $\le 200A/uS$, Vdd $\le BV$, Starting $T_J = 25 \ ^{o}C$.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM8N80CZ C0G	TO-220	50pcs / Tube
TSM8N80CI C0G	ITO-220	50pcs / Tube

Note:

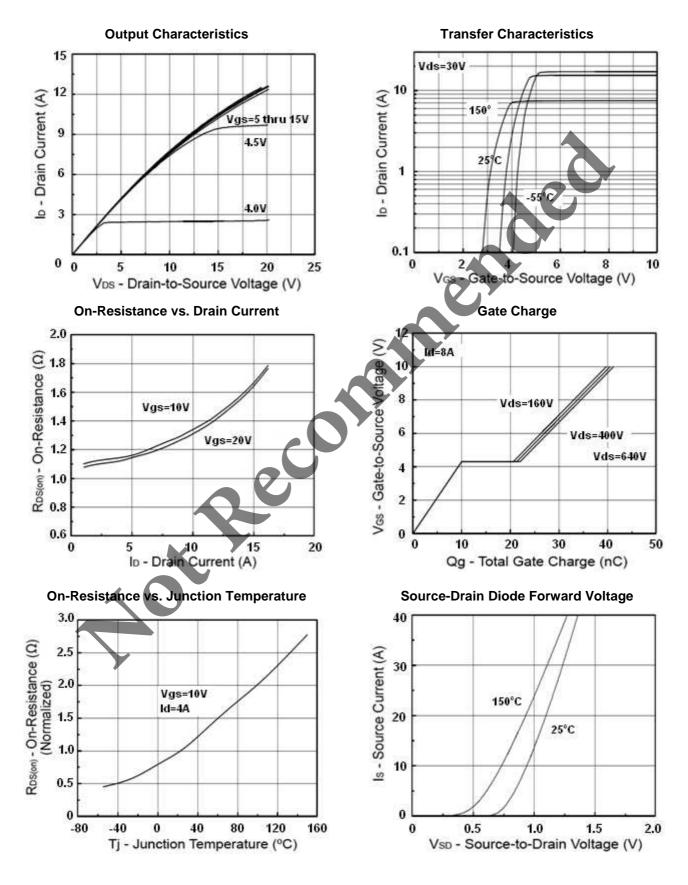
ot Reconnection 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

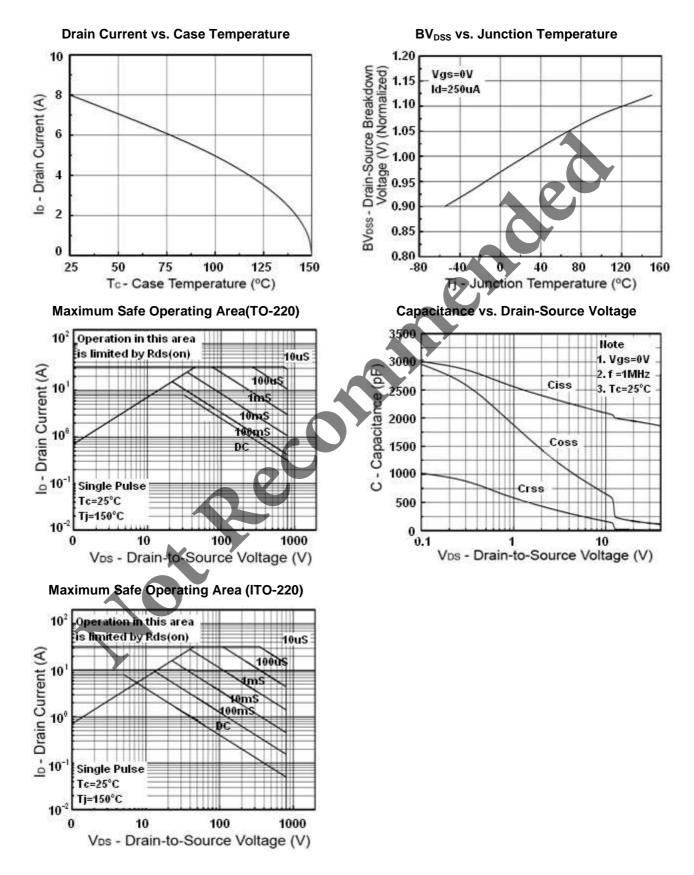
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





CHARACTERISTICS CURVES

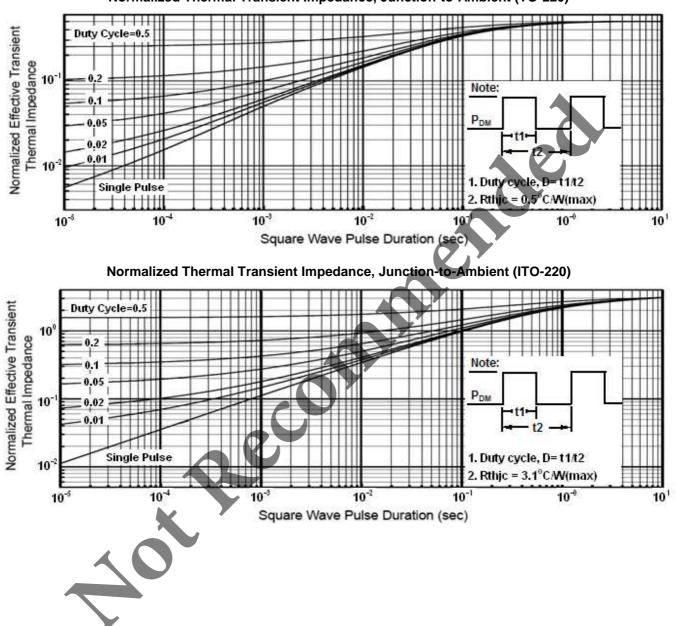
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





ELECTRICAL CHARACTERISTICS CURVES

 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

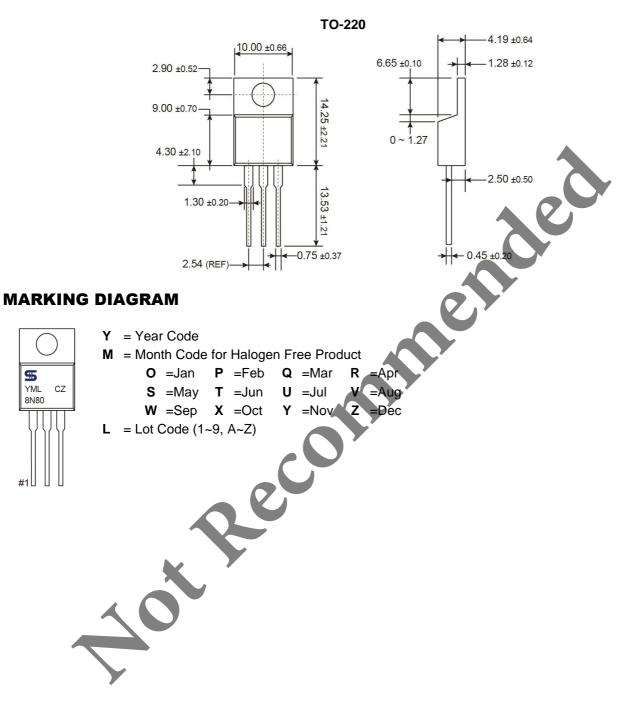




TAIWAN

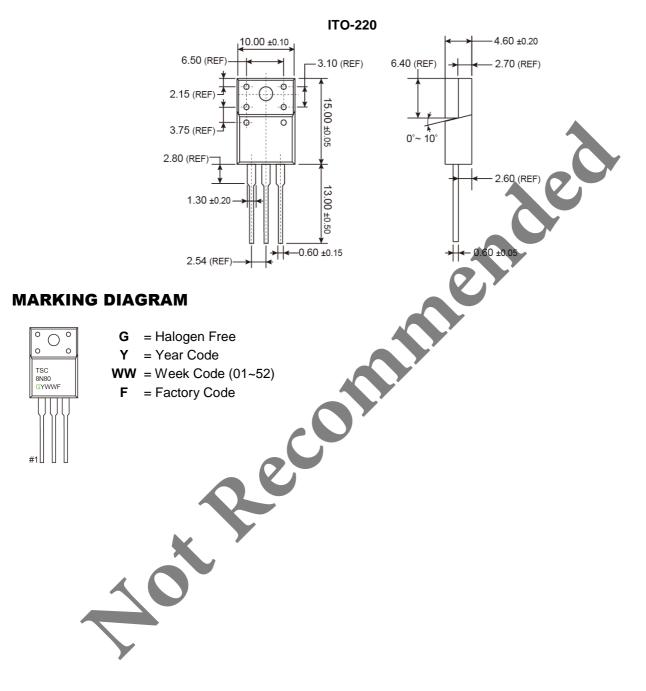
MICONDUCTOR

9





PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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